

FIG.1

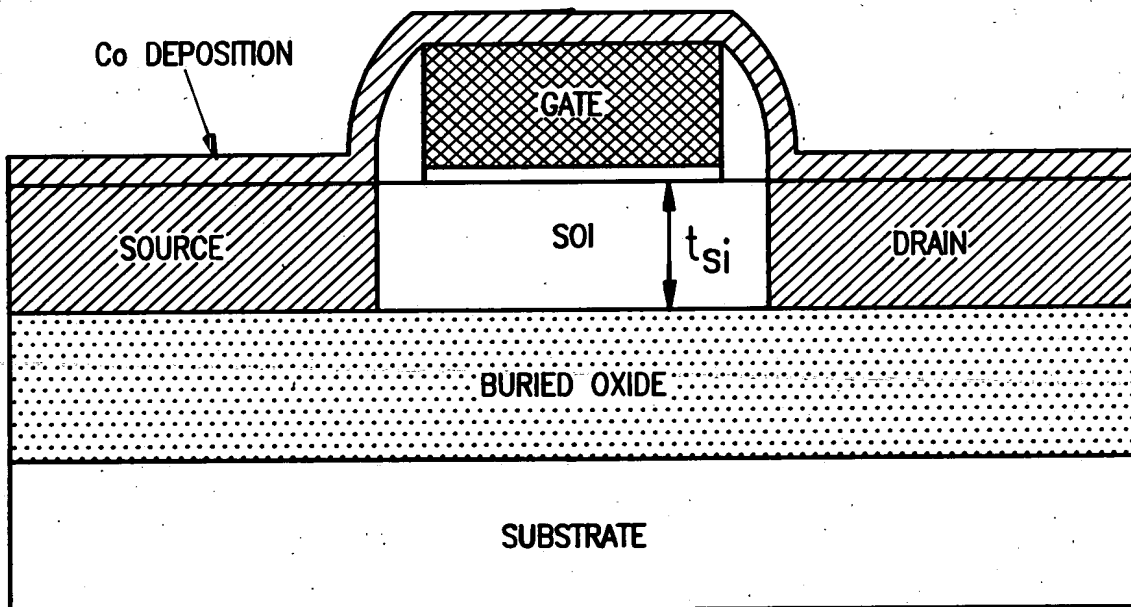


FIG.2

T06T60"E3H20660

FORM Co_2Si BY LOW TEMPERATURE ANNEAL

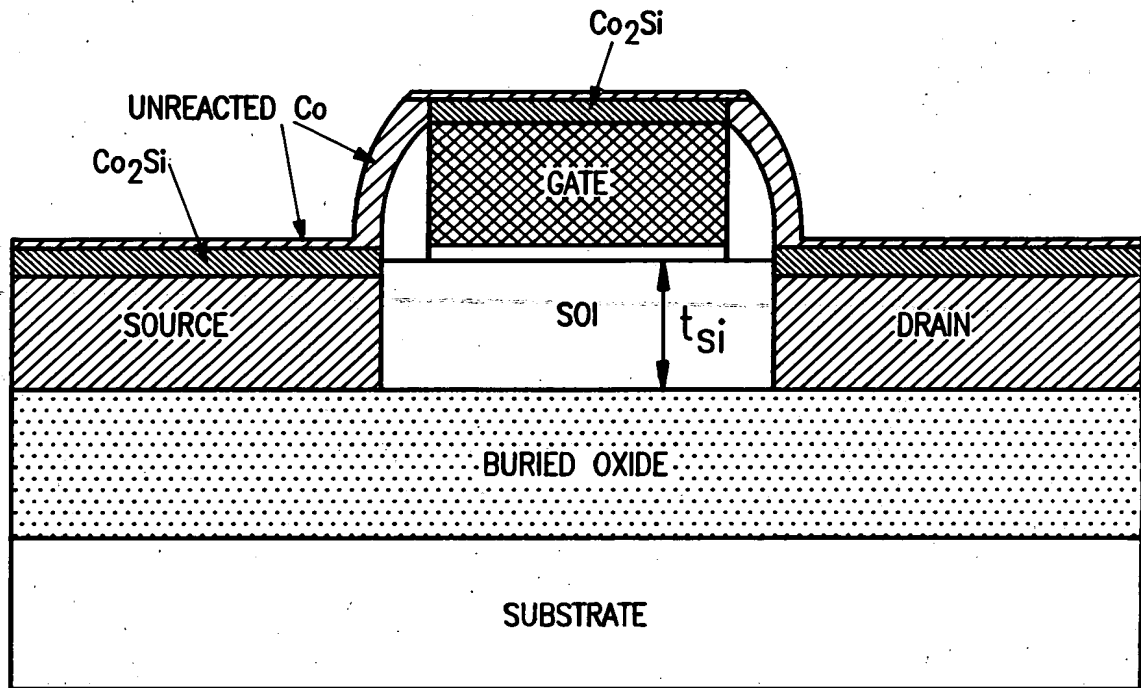


FIG.3

DEPOSITE $\alpha\text{-Si}$

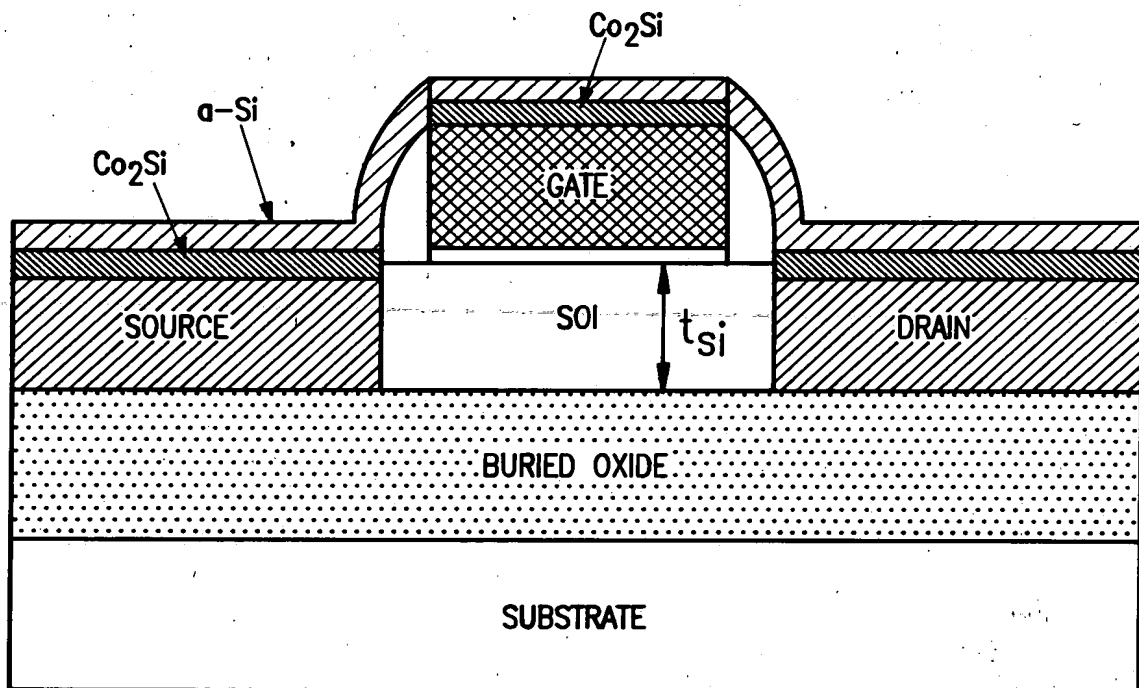


FIG.4

TOP SECRET E8420660

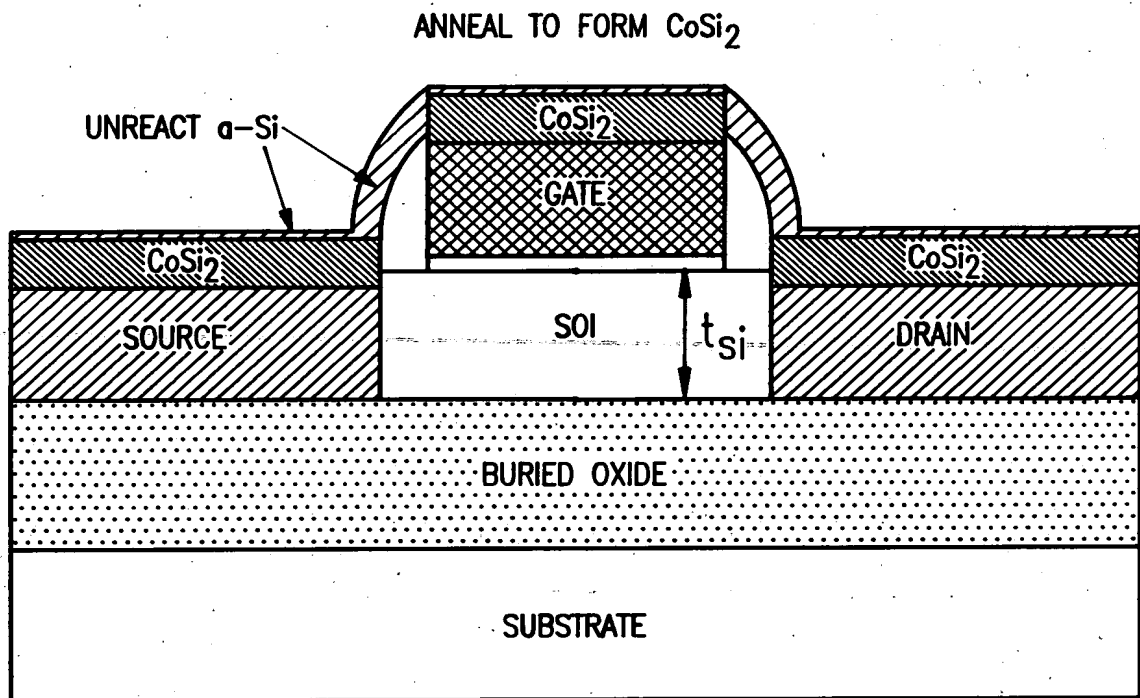


FIG.5

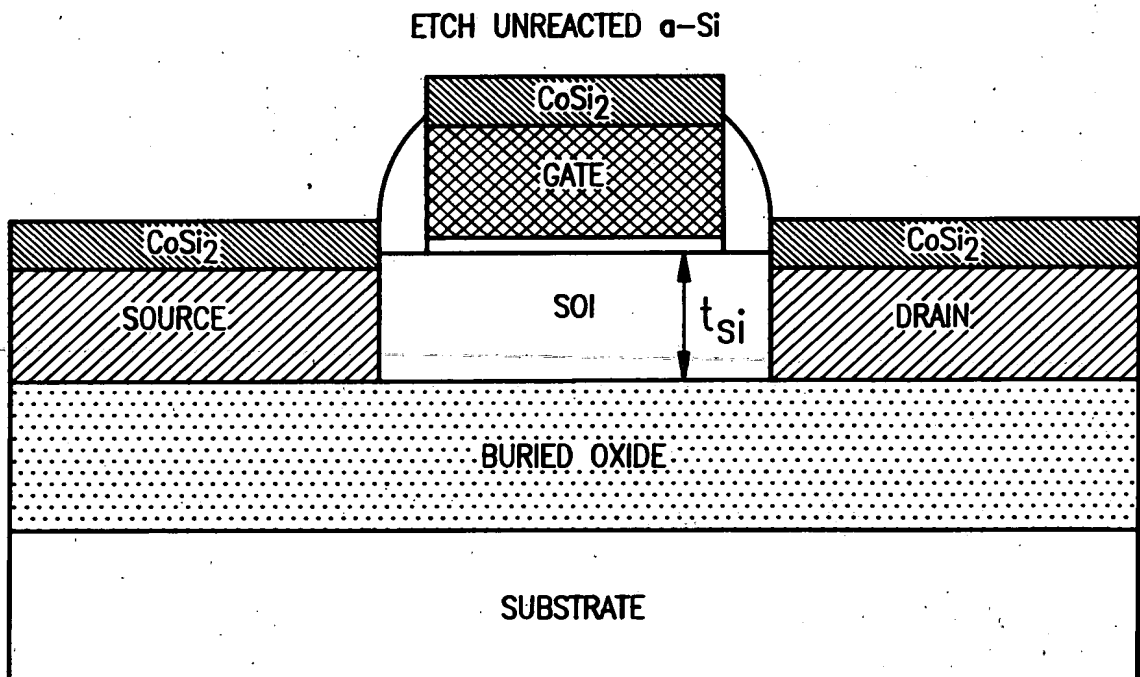


FIG.6

106160-23420660

FIG.7A

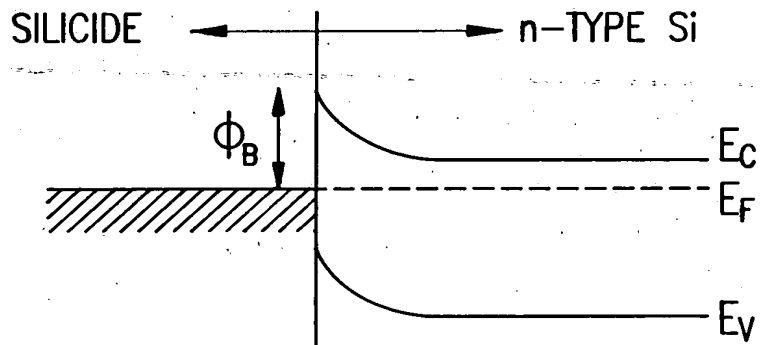
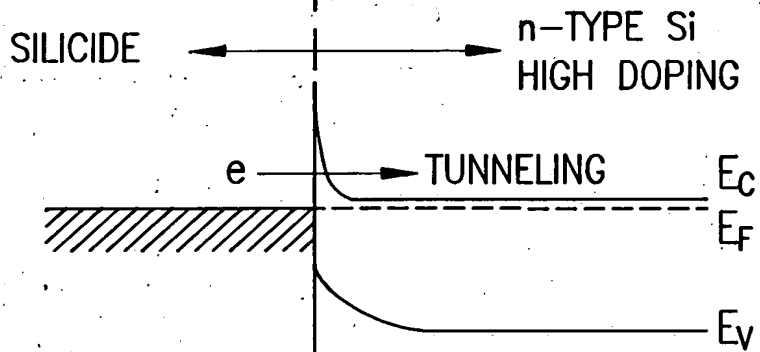
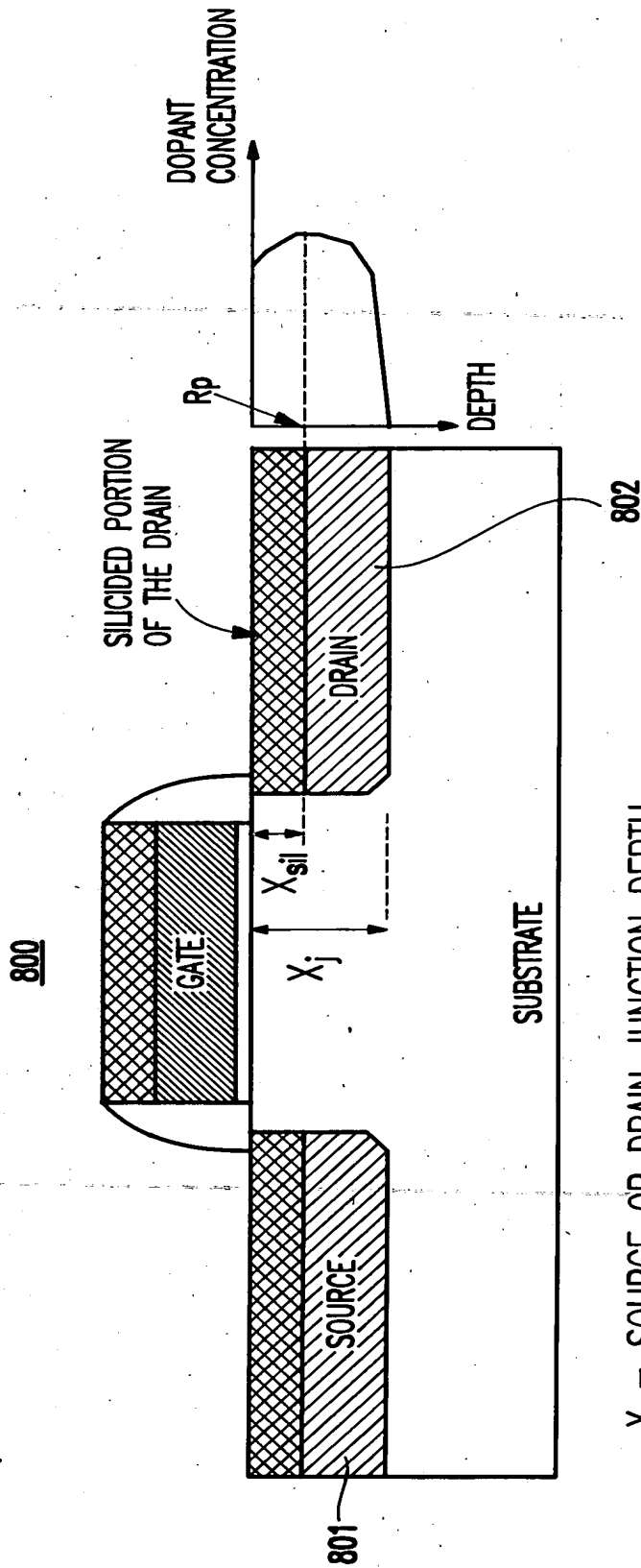


FIG.7B





X_j = SOURCE OR DRAIN JUNCTION DEPTH

X_{sil} = SILICIDE JUNCTION DEPTH

R_p = PEAK DOPANT CONCENTRATION

REQUIREMENTS:

1. $X_j > X_{sil}$
2. X_{sil} ROUGHLY EQUALS R_p

FIG.8

